Welcome to E-XFL.COM

What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	168MHz
Connectivity	CANbus, DCMI, EBI/EMI, Ethernet, I²C, IrDA, LINbus, SPI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, I²S, LCD, POR, PWM, WDT
Number of I/O	82
Program Memory Size	1MB (1M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	192K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 16x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	-
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f417vgt6tr

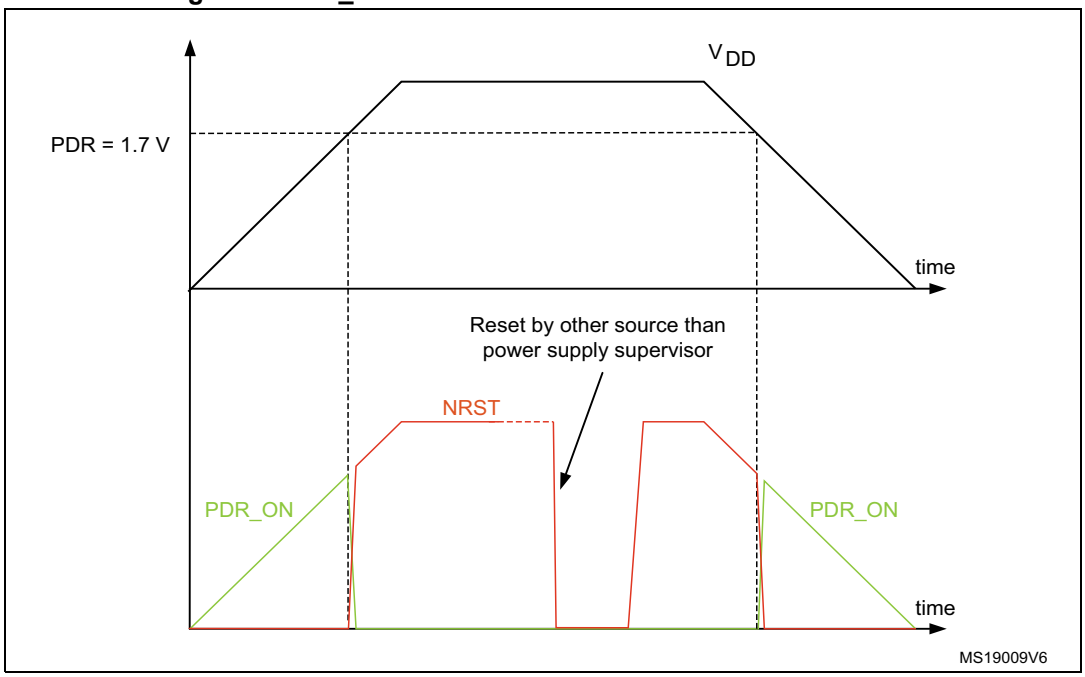
1 Introduction

This datasheet provides the description of the STM32F415xx and STM32F417xx lines of microcontrollers. For more details on the whole STMicroelectronics STM32™ family, please refer to *Section 2.1: Full compatibility throughout the family*.

The STM32F415xx and STM32F417xx datasheet should be read in conjunction with the STM32F4xx reference manual which is available from the STMicroelectronics website *www.st.com*.

For information on the Cortex®-M4 core, please refer to the Cortex®-M4 programming manual (PM0214) available from *www.st.com*.

Figure 8. PDR_ON and NRST control with internal reset OFF



1. PDR = 1.7 V for reduce temperature range; PDR = 1.8 V for all temperature range.

2.2.16 Voltage regulator

The regulator has four operating modes:

- Regulator ON
  - Main regulator mode (MR)
  - Low-power regulator (LPR)
  - Power-down
- Regulator OFF

Regulator ON

On packages embedding the BYPASS_REG pin, the regulator is enabled by holding BYPASS_REG low. On all other packages, the regulator is always enabled.

There are three power modes configured by software when regulator is ON:

- MR is used in the nominal regulation mode (With different voltage scaling in Run)

  In Main regulator mode (MR mode), different voltage scaling are provided to reach the best compromise between maximum frequency and dynamic power consumption. Refer to *Table 14: General operating conditions*.
- LPR is used in the Stop modes

  The LP regulator mode is configured by software when entering Stop mode.
- Power-down is used in Standby mode.

  The Power-down mode is activated only when entering in Standby mode. The regulator output is in high impedance and the kernel circuitry is powered down, inducing zero consumption. The contents of the registers and SRAM are lost)

2.2.40 Embedded Trace Macrocell™

The ARM Embedded Trace Macrocell provides a greater visibility of the instruction and data flow inside the CPU core by streaming compressed data at a very high rate from the STM32F41xxx through a small number of ETM pins to an external hardware trace port analyser (TPA) device. The TPA is connected to a host computer using USB, Ethernet, or any other high-speed channel. Real-time instruction and data flow activity can be recorded and then formatted for display on the host computer that runs the debugger software. TPA hardware is commercially available from common development tool vendors.

The Embedded Trace Macrocell operates with third party debugger software tools.

Table 7. STM32F41xxx pin and ball definitions (continued)

Pin number						Pin name (function after reset)(1)	Pin type	I / O structure	Notes	Alternate functions	Additional functions
LQFP64	WLCSP90	LQFP100	LQFP144	UFBGA176	LQFP176						
-	-	-	11	H3	17	PF1	I/O	FT	-	FSMC_A1 / I2C2_SCL / EVENTOUT	-
-	-	-	12	H2	18	PF2	I/O	FT	-	FSMC_A2 / I2C2_SMBA / EVENTOUT	-
-	-	-	13	J2	19	PF3	I/O	FT	(4)	FSMC_A3/EVENTOUT	ADC3_IN9
-	-	-	14	J3	20	PF4	I/O	FT	(4)	FSMC_A4/EVENTOUT	ADC3_IN14
-	-	-	15	K3	21	PF5	I/O	FT	(4)	FSMC_A5/EVENTOUT	ADC3_IN15
-	C9	10	16	G2	22	V_{SS}	S	-	-	-	-
-	B8	11	17	G3	23	V_{DD}	S	-	-	-	-
-	-	-	18	K2	24	PF6	I/O	FT	(4)	TIM10_CH1 / FSMC_NIORD/ EVENTOUT	ADC3_IN4
-	-	-	19	K1	25	PF7	I/O	FT	(4)	TIM11_CH1/FSMC_NREG/ EVENTOUT	ADC3_IN5
-	-	-	20	L3	26	PF8	I/O	FT	(4)	TIM13_CH1 / FSMC_NIOWR/ EVENTOUT	ADC3_IN6
-	-	-	21	L2	27	PF9	I/O	FT	(4)	TIM14_CH1 / FSMC_CD/ EVENTOUT	ADC3_IN7
-	-	-	22	L1	28	PF10	I/O	FT	(4)	FSMC_INTR/ EVENTOUT	ADC3_IN8
5	F10	12	23	G1	29	PH0/OSC_IN (PH0)	I/O	FT	-	EVENTOUT	OSC_IN(4)
6	F9	13	24	H1	30	PH1/OSC_OUT (PH1)	I/O	FT	-	EVENTOUT	OSC_OUT(4)
7	G10	14	25	J1	31	NRST	I/O	RST	-	-	-
8	E10	15	26	M2	32	PC0	I/O	FT	(4)	OTG_HS_ULPI_STP/ EVENTOUT	ADC123_IN10
9	-	16	27	M3	33	PC1	I/O	FT	(4)	ETH_MDC/ EVENTOUT	ADC123_IN11
10	D10	17	28	M4	34	PC2	I/O	FT	(4)	SPI2_MISO / OTG_HS_ULPI_DIR / ETH_MII_TXD2 /I2S2ext_SD/ EVENTOUT	ADC123_IN12

Table 7. STM32F41xxx pin and ball definitions (continued)

Pin number						Pin name (function after reset)(1)	Pin type	I / O structure	Notes	Alternate functions	Additional functions
LQFP64	WLCSP90	LQFP100	LQFP144	UFBGA176	LQFP176						
40	E3	66	99	F14	118	PC9	I/O	FT	-	I2S_CKIN/ MCO2 / TIM8_CH4/SDIO_D1 / /I2C3_SDA / DCMI_D3 / TIM3_CH4/ EVENTOUT	-
41	D1	67	100	F15	119	PA8	I/O	FT	-	MCO1 / USART1_CK/ TIM1_CH1/ I2C3_SCL/ OTG_FS_SOF/ EVENTOUT	-
42	D2	68	101	E15	120	PA9	I/O	FT	-	USART1_TX/ TIM1_CH2 / I2C3_SMBA / DCMI_D0/ EVENTOUT	OTG_FS_VBUS
43	D3	69	102	D15	121	PA10	I/O	FT	-	USART1_RX/ TIM1_CH3/ OTG_FS_ID/DCMI_D1/ EVENTOUT	-
44	C1	70	103	C15	122	PA11	I/O	FT	-	USART1_CTS / CAN1_RX / TIM1_CH4 / OTG_FS_DM/ EVENTOUT	-
45	C2	71	104	B15	123	PA12	I/O	FT	-	USART1_RTS / CAN1_TX/ TIM1_ETR/ OTG_FS_DP/ EVENTOUT	-
46	D4	72	105	A15	124	PA13 (JTMS-SWDIO)	I/O	FT	-	JTMS-SWDIO/ EVENTOUT	-
47	B1	73	106	F13	125	V_{CAP_2}	S	-	-	-	-
-	E7	74	107	F12	126	V_{SS}	S	-	-	-	-
48	E6	75	108	G13	127	V_{DD}	S	-	-	-	-
-	-	-	-	E12	128	PH13	I/O	FT	-	TIM8_CH1N / CAN1_TX/ EVENTOUT	-
-	-	-	-	E13	129	PH14	I/O	FT	-	TIM8_CH2N / DCMI_D4/ EVENTOUT	-
-	-	-	-	D13	130	PH15	I/O	FT	-	TIM8_CH3N / DCMI_D11/ EVENTOUT	-
-	C3	-	-	E14	131	PI0	I/O	FT	-	TIM5_CH4 / SPI2_NSS / I2S2_WS / DCMI_D13/ EVENTOUT	-
-	B2	-	-	D14	132	PI1	I/O	FT	-	SPI2_SCK / I2S2_CK / DCMI_D8/ EVENTOUT	-

Table 7. STM32F41xxx pin and ball definitions (continued)

Pin number						Pin name (function after reset)(1)	Pin type	I / O structure	Notes	Alternate functions	Additional functions
LQFP64	WLCSP90	LQFP100	LQFP144	UFBGA176	LQFP176						
-	A8	-	143	C6	171	PDR_ON	I	FT	-	-	-
64	A1	100	144	C5	172	V_{DD}	S	-	-	-	-
-	-	-	-	D4	173	PI4	I/O	FT	-	TIM8_BKIN / DCMI_D5/ EVENTOUT	-
-	-	-	-	C4	174	PI5	I/O	FT	-	TIM8_CH1 / DCMI_VSYNC/ EVENTOUT	-
-	-	-	-	C3	175	PI6	I/O	FT	-	TIM8_CH2 / DCMI_D6/ EVENTOUT	-
-	-	-	-	C2	176	PI7	I/O	FT	-	TIM8_CH3 / DCMI_D7/ EVENTOUT	-

1. Function availability depends on the chosen device.
2. PC13, PC14, PC15 and PI8 are supplied through the power switch. Since the switch only sinks a limited amount of current (3 mA), the use of GPIOs PC13 to PC15 and PI8 in output mode is limited:
   - The speed should not exceed 2 MHz with a maximum load of 30 pF.
   - These I/Os must not be used as a current source (e.g. to drive an LED).
3. Main function after the first backup domain power-up. Later on, it depends on the contents of the RTC registers even after reset (because these registers are not reset by the main reset). For details on how to manage these I/Os, refer to the RTC register description sections in the STM32F4xx reference manual, available from the STMicroelectronics website: *www.st.com*.
4. FT = 5 V tolerant except when in analog mode or oscillator mode (for PC14, PC15, PH0 and PH1).
5. If the device is delivered in an UFBGA176 or WLCSP90 and the BYPASS_REG pin is set to VDD (Regulator off/internal reset ON mode), then PA0 is used as an internal Reset (active low).

Table 8. FSMC pin definition

Pins(1)	FSMC				LQFP100(2)	WLCSP90 (2)
	CF	NOR/PSRAM/ SRAM	NOR/PSRAM Mux	NAND 16 bit		
PE2	-	A23	A23	-	Yes	-
PE3	-	A19	A19	-	Yes	-
PE4	-	A20	A20	-	Yes	-
PE5	-	A21	A21	-	Yes	-
PE6	-	A22	A22	-	Yes	-
PF0	A0	A0	-	-	-	-

Table 9. Alternate function mapping

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15
		SYS	TIM1/2	TIM3/4/5	TIM8/9/10 /11	I2C1/2/3	SPI1/SPI2/ I2S2/I2S2e xt	SPI3/I2Sext /I2S3	USART1/2/3/ I2S3ext	UART4/5/ USART6	CAN1/2 TIM12/13/ 14	OTG_FS/ OTG_HS	ETH	FSMC/SDIO /OTG_FS	DCMI		
Port A	PA0	-	TIM2_CH1_ ETR	TIM 5_CH1	TIM8_ETR	-	-	-	USART2_CTS	UART4_TX	-	-	ETH_MII_CRS	-	-	-	EVENTOUT
	PA1	-	TIM2_CH2	TIM5_CH2	-	-	-	-	USART2_RTS	UART4_RX	-	-	ETH_MII _RX_CLK ETH_RMII__REF _CLK	-	-	-	EVENTOUT
	PA2	-	TIM2_CH3	TIM5_CH3	TIM9_CH1	-	-	-	USART2_TX	-	-	-	ETH_MDIO	-	-	-	EVENTOUT
	PA3	-	TIM2_CH4	TIM5_CH4	TIM9_CH2	-	-	-	USART2_RX	-	-	OTG_HS_ULPI_ D0	ETH _MII_COL	-	-	-	EVENTOUT
	PA4	-	-	-	-	-	SPI1_NSS	SPI3_NSS I2S3_WS	USART2_CK	-	-	-	-	OTG_HS_SOF	DCMI_ HSYNC	-	EVENTOUT
	PA5	-	TIM2_CH1_ ETR	-	TIM8_CH1N	-	SPI1_SCK	-	-	-	-	OTG_HS_ULPI_ CK	-	-	-	-	EVENTOUT
	PA6	-	TIM1_BKIN	TIM3_CH1	TIM8_BKIN	-	SPI1_MISO	-	-	-	TIM13_CH1	-	-	-	DCMI_PIXCK	-	EVENTOUT
	PA7	-	TIM1_CH1N	TIM3_CH2	TIM8_CH1N	-	SPI1_MOSI	-	-	-	TIM14_CH1	-	ETH_MII _RX_DV ETH_RMII _CRS_DV	-	-	-	EVENTOUT
	PA8	MCO1	TIM1_CH1	-	-	I2C3_SCL	-	-	USART1_CK	-	-	OTG_FS_SOF	-	-	-	-	EVENTOUT
	PA9	-	TIM1_CH2	-	-	I2C3_ SMBA	-	-	USART1_TX	-	-	-	-	-	DCMI_D0	-	EVENTOUT
	PA10	-	TIM1_CH3	-	-	-	-	-	USART1_RX	-	-	OTG_FS_ID	-	-	DCMI_D1	-	EVENTOUT
	PA11	-	TIM1_CH4	-	-	-	-	-	USART1_CTS	-	CAN1_RX	OTG_FS_DM	-	-	-	-	EVENTOUT
	PA12	-	TIM1_ETR	-	-	-	-	-	USART1_RTS	-	CAN1_TX	OTG_FS_DP	-	-	-	-	EVENTOUT
	PA13	JTMS-SWDIO	-	-	-	-	-	-	-	-	-	-	-	-	-	-	EVENTOUT
	PA14	JTCK-SWCLK	-	-	-	-	-	-	-	-	-	-	-	-	-	-	EVENTOUT
	PA15	JTDI	TIM 2_CH1 TIM 2_ETR	-	-	-	SPI1_NSS	SPI3_NSS/ I2S3_WS	-	-	-	-	-	-	-	-	EVENTOUT

Table 9. Alternate function mapping (continued)

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15
		SYS	TIM1/2	TIM3/4/5	TIM8/9/10/11	I2C1/2/3	SPI1/SPI2/I2S2/I2S2ext	SPI3/I2Sext/I2S3	USART1/2/3/I2S3ext	UART4/5/USART6	CAN1/2 TIM12/13/14	OTG_FS/OTG_HS	ETH	FSMC/SDIO/OTG_FS	DCMI		
Port I	PI0	-	-	TIM5_CH4	-	-	SPI2_NSS I2S2_WS	-	-	-	-	-	-	-	DCMI_D13	-	EVENTOUT
	PI1	-	-	-	-	-	SPI2_SCK I2S2_CK	-	-	-	-	-	-	-	DCMI_D8	-	EVENTOUT
	PI2	-	-	-	TIM8_CH4	-	SPI2_MISO	I2S2ext_SD	-	-	-	-	-	-	DCMI_D9	-	EVENTOUT
	PI3	-	-	-	TIM8_ETR	-	SPI2_MOSI I2S2_SD	-	-	-	-	-	-	-	DCMI_D10	-	EVENTOUT
	PI4	-	-	-	TIM8_BKIN	-	-	-	-	-	-	-	-	-	DCMI_D5	-	EVENTOUT
	PI5	-	-	-	TIM8_CH1	-	-	-	-	-	-	-	-	-	DCMI_VSYNC	-	EVENTOUT
	PI6	-	-	-	TIM8_CH2	-	-	-	-	-	-	-	-	-	DCMI_D6	-	EVENTOUT
	PI7	-	-	-	TIM8_CH3	-	-	-	-	-	-	-	-	-	DCMI_D7	-	EVENTOUT
	PI8	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	EVENTOUT
	PI9	-	-	-	-	-	-	-	-	-	CAN1_RX	-	-	-	-	-	EVENTOUT
	PI10	-	-	-	-	-	-	-	-	-	-	-	ETH _MII_RX_ER	-	-	-	EVENTOUT
	PI11	-	-	-	-	-	-	-	-	-	-	OTG_HS_ULPI_DIR	-	-	-	-	EVENTOUT

Table 12. Current characteristics

Symbol	Ratings	Max.	Unit
I_{VDD}	Total current into V_{DD} power lines (source)(1)	240	mA
I_{VSS}	Total current out of V_{SS} ground lines (sink)(1)	240	
I_{IO}	Output current sunk by any I/O and control pin	25	
	Output current source by any I/Os and control pin	25	
$I_{INJ(PIN)}$ (2)	Injected current on five-volt tolerant I/O(3)	–5/+0	
	Injected current on any other pin(4)	±5	
$\Sigma I_{INJ(PIN)}$(4)	Total injected current (sum of all I/O and control pins)(5)	±25	

1. All main power (V_{DD}, V_{DDA}) and ground (V_{SS}, V_{SSA}) pins must always be connected to the external power supply, in the permitted range.
2. Negative injection disturbs the analog performance of the device. See note in *Section 5.3.21: 12-bit ADC characteristics*.
3. Positive injection is not possible on these I/Os. A negative injection is induced by $V_{IN}<V_{SS}$. $I_{INJ(PIN)}$ must never be exceeded. Refer to *Table 11* for the values of the maximum allowed input voltage.
4. A positive injection is induced by $V_{IN}>V_{DD}$ while a negative injection is induced by $V_{IN}<V_{SS}$. $I_{INJ(PIN)}$ must never be exceeded. Refer to *Table 11* for the values of the maximum allowed input voltage.
5. When several inputs are submitted to a current injection, the maximum $\Sigma I_{INJ(PIN)}$ is the absolute sum of the positive and negative injected currents (instantaneous values).

Table 13. Thermal characteristics

Symbol	Ratings	Value	Unit
T_{STG}	Storage temperature range	–65 to +150	°C
T_J	Maximum junction temperature	125	°C

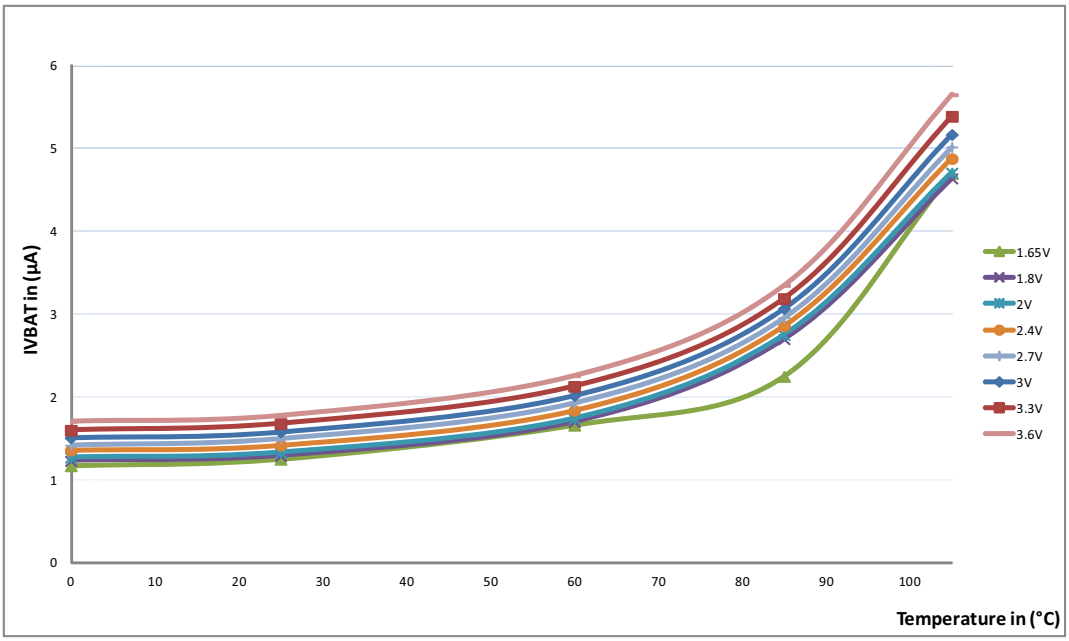
5.3 Operating conditions

5.3.1 General operating conditions

Table 14. General operating conditions

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{HCLK}	Internal AHB clock frequency	VOS bit in PWR_CR register = 0(1)	0	-	144	MHz
		VOS bit in PWR_CR register= 1	0	-	168	
f_{PCLK1}	Internal APB1 clock frequency	-	0	-	42	
f_{PCLK2}	Internal APB2 clock frequency	-	0	-	84	
V_{DD}	Standard operating voltage	-	1.8(2)	-	3.6	V
V_{DDA}(3)(4)	Analog operating voltage (ADC limited to 1.2 M samples)	Must be the same potential as V_{DD}(5)	1.8(2)	-	2.4	V
	Analog operating voltage (ADC limited to 1.4 M samples)		2.4	-	3.6	
V_{BAT}	Backup operating voltage	-	1.65	-	3.6	V

Figure 29. Typical V_{BAT} current consumption (LSE and RTC ON/backup RAM ON)



Additional current consumption

The MCU is placed under the following conditions:

- All I/O pins are configured in analog mode.
- The Flash memory access time is adjusted to f_{HCLK} frequency.
- The voltage scaling is adjusted to f_{HCLK} frequency as follows:
  - Scale 2 for $f_{HCLK} \leq 144$ MHz
  - Scale 1 for 144 MHz < $f_{HCLK} \leq 168$ MHz.
- The system clock is HCLK, $f_{PCLK1} = f_{HCLK}/4$, and $f_{PCLK2} = f_{HCLK}/2$.
- The HSE crystal clock frequency is 25 MHz.
- T_A= 25 °C.

Table 26. Typical current consumption in Run mode, code with data processing running from Flash memory, regulator ON (ART accelerator enabled except prefetch), V_{DD} = 1.8 V(1)

Symbol	Parameter	Conditions	f_{HCLK} (MHz)	Typ. at T_A = 25 °C	Unit
IDD	Supply current in Run mode	All peripheral disabled	160	36.2	mA
			144	29.3	
			120	24.7	
			90	19.3	
			60	13.4	
			30	7.7	
			25	6.0	

1. When peripherals are enabled, the power consumption corresponding to the analog part of the peripherals (such as ADC or DAC) is not included.

I/O system current consumption

The current consumption of the I/O system has two components: static and dynamic.

I/O static current consumption

All the I/Os used as inputs with pull-up generate current consumption when the pin is externally held low. The value of this current consumption can be simply computed by using the pull-up/pull-down resistors values given in *Table 48: I/O static characteristics*.

For the output pins, any external pull-down or external load must also be considered to estimate the current consumption.

Additional I/O current consumption is due to I/Os configured as inputs if an intermediate voltage level is externally applied. This current consumption is caused by the input Schmitt trigger circuits used to discriminate the input value. Unless this specific configuration is required by the application, this supply current consumption can be avoided by configuring these I/Os in analog mode. This is notably the case of ADC input pins which should be configured as analog inputs.

Caution: Any floating input pin can also settle to an intermediate voltage level or switch inadvertently, as a result of external electromagnetic noise. To avoid current consumption related to

floating pins, they must either be configured in analog mode, or forced internally to a definite digital value. This can be done either by using pull-up/down resistors or by configuring the pins in output mode.

I/O dynamic current consumption

In addition to the internal peripheral current consumption measured previously (see *Table 28: Peripheral current consumption*), the I/Os used by an application also contribute to the current consumption. When an I/O pin switches, it uses the current from the MCU supply voltage to supply the I/O pin circuitry and to charge/discharge the capacitive load (internal or external) connected to the pin:

$$I_{SW} = V_{DD} \times f_{SW} \times C$$

where

I_{SW} is the current sunk by a switching I/O to charge/discharge the capacitive load

V_{DD} is the MCU supply voltage

f_{SW} is the I/O switching frequency

C is the total capacitance seen by the I/O pin: $C = C_{INT} + C_{EXT}$

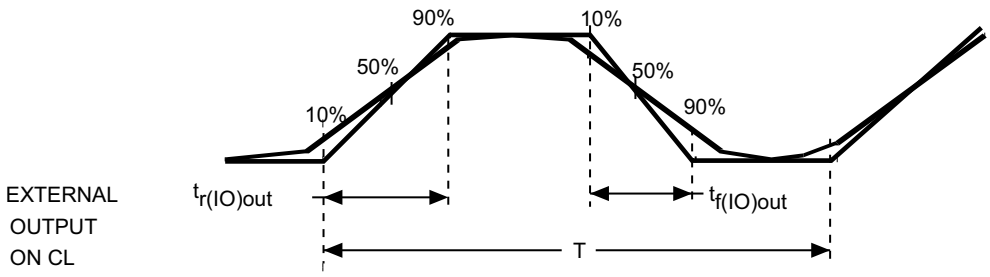
The test pin is configured in push-pull output mode and is toggled by software at a fixed frequency.

Table 50. I/O AC characteristics[1][2] (continued)

OSPEEDRy [1:0] bit value[1]	Symbol	Parameter	Conditions	Min	Typ	Max	Unit
11	$F_{max(IO)out}$	Maximum frequency[3]	C_L = 30 pF, V_{DD} > 2.70 V	-	-	100[4]	MHz
			C_L = 30 pF, V_{DD} > 1.8 V	-	-	50[4]	
			C_L = 10 pF, V_{DD} > 2.70 V	-	-	180[4]	
			C_L = 10 pF, V_{DD} > 1.8 V	-	-	100[4]	
	$t_{f(IO)out}$/ $t_{r(IO)out}$	Output high to low level fall time and output low to high level rise time	C_L = 30 pF, V_{DD} > 2.70 V	-	-	4	ns
			C_L = 30 pF, V_{DD} > 1.8 V	-	-	6	
			C_L = 10 pF, V_{DD} > 2.70 V	-	-	2.5	
			C_L = 10 pF, V_{DD} > 1.8 V	-	-	4	
-	t_{EXTIpw}	Pulse width of external signals detected by the EXTI controller		10	-	-	ns

1. Guaranteed by characterization.
2. The I/O speed is configured using the OSPEEDRy[1:0] bits. Refer to the STM32F4xx reference manual for a description of the GPIOx_SPEEDR GPIO port output speed register.
3. The maximum frequency is defined in *Figure 37*.
4. For maximum frequencies above 50 MHz, the compensation cell should be used.

Figure 37. I/O AC characteristics definition



Maximum frequency is achieved if (t_r + t_f) ≤ (2/3)T and if the duty cycle is (45-55%) when loaded by CL specified in the table " *I/O AC characteristics*".

ai14131d

Equation 1: R_{AIN} max formula

$$R_{AIN} = \frac{(k - 0.5)}{f_{ADC} \times C_{ADC} \times \ln(2^{N+2})} - R_{ADC}$$

The formula above (*Equation 1*) is used to determine the maximum external impedance allowed for an error below 1/4 of LSB. N = 12 (from 12-bit resolution) and k is the number of sampling periods defined in the ADC_SMPR1 register.

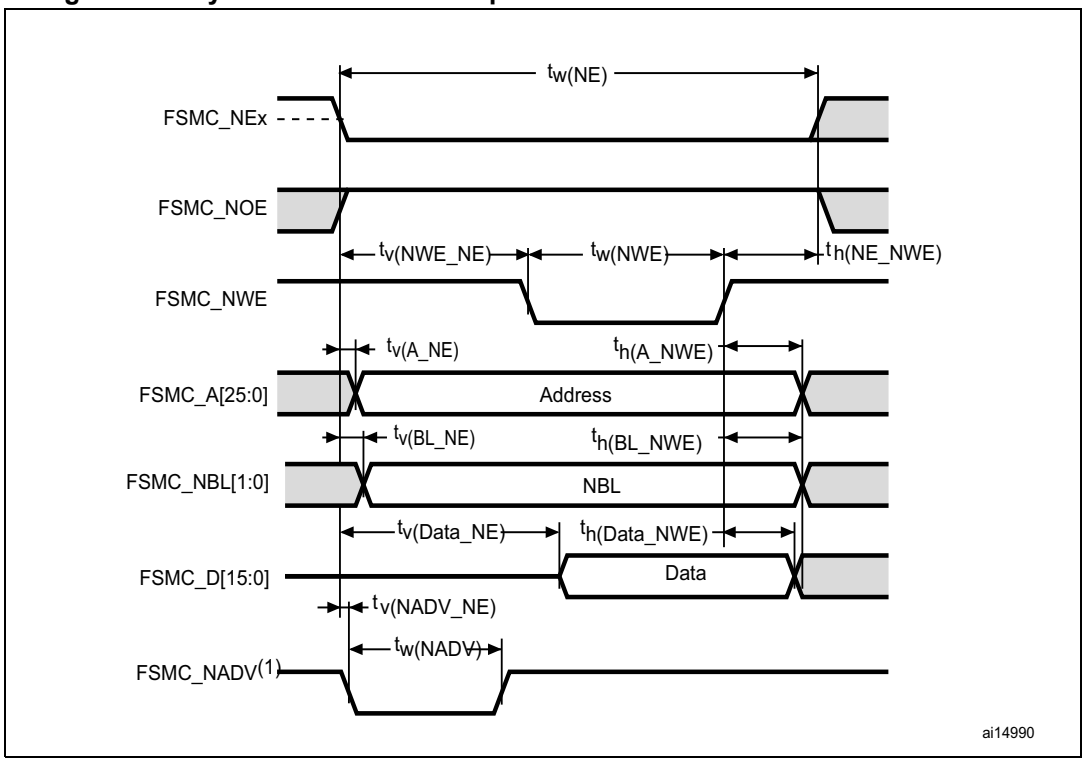
Table 68. ADC accuracy at f_{ADC} = 30 MHz

Symbol	Parameter	Test conditions	Typ	Max(1)	Unit
ET	Total unadjusted error	f_{PCLK2} = 60 MHz, f_{ADC} = 30 MHz, R_{AIN} < 10 kΩ, V_{DDA} = 1.8(2) to 3.6 V	±2	±5	LSB
EO	Offset error		±1.5	±2.5	
EG	Gain error		±1.5	±3	
ED	Differential linearity error		±1	±2	
EL	Integral linearity error		±1.5	±3	

1. Guaranteed by characterization.
2. V_{DD}/V_{DDA} minimum value of 1.7 V is obtained when the device operates in reduced temperature range, and with the use of an external power supply supervisor (refer to *Section : Internal reset OFF*).

Note: ADC accuracy vs. negative injection current: injecting a negative current on any analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative currents.
Any positive injection current within the limits specified for $I_{INJ(PIN)}$ and $SI_{INJ(PIN)}$ in Section 5.3.16 does not affect the ADC accuracy.

Figure 55. Asynchronous non-multiplexed SRAM/PSRAM/NOR write waveforms



1. Mode 2/B, C and D only. In Mode 1, FSMC_NADV is not used.

Table 76. Asynchronous non-multiplexed SRAM/PSRAM/NOR write timings(1)(2)

Symbol	Parameter	Min	Max	Unit
$t_{w(NE)}$	FSMC_NE low time	$3T_{HCLK}$	$3T_{HCLK}+4$	ns
$t_{v(NWE\_NE)}$	FSMC_NEx low to FSMC_NWE low	$T_{HCLK}-0.5$	$T_{HCLK}+0.5$	ns
$t_{w(NWE)}$	FSMC_NWE low time	$T_{HCLK}-1$	$T_{HCLK}+2$	ns
$t_{h(NE\_NWE)}$	FSMC_NWE high to FSMC_NE high hold time	$T_{HCLK}-1$	-	ns
$t_{v(A\_NE)}$	FSMC_NEx low to FSMC_A valid	-	0	ns
$t_{h(A\_NWE)}$	Address hold time after FSMC_NWE high	$T_{HCLK}-2$	-	ns
$t_{v(BL\_NE)}$	FSMC_NEx low to FSMC_BL valid	-	1.5	ns
$t_{h(BL\_NWE)}$	FSMC_BL hold time after FSMC_NWE high	$T_{HCLK}-1$	-	ns
$t_{v(Data\_NE)}$	Data to FSMC_NEx low to Data valid	-	$T_{HCLK}+3$	ns
$t_{h(Data\_NWE)}$	Data hold time after FSMC_NWE high	$T_{HCLK}-1$	-	ns
$t_{v(NADV\_NE)}$	FSMC_NEx low to FSMC_NADV low	-	2	ns
$t_{w(NADV)}$	FSMC_NADV low time	-	$T_{HCLK}+0.5$	ns

1. C_L = 30 pF.
2. Guaranteed by characterization.

2. Guaranteed by characterization.

Synchronous waveforms and timings

Figure 58 through *Figure 61* represent synchronous waveforms and *Table 80* through *Table 82* provide the corresponding timings. The results shown in these tables are obtained with the following FSMC configuration:

- BurstAccessMode = FSMC_BurstAccessMode_Enable;
- MemoryType = FSMC_MemoryType_CRAM;
- WriteBurst = FSMC_WriteBurst_Enable;
- CLKDivision = 1; (0 is not supported, see the STM32F40xxx/41xxx reference manual)
- DataLatency = 1 for NOR Flash; DataLatency = 0 for PSRAM

In all timing tables, the T_{HCLK} is the HCLK clock period (with maximum FSMC_CLK = 60 MHz).

Figure 58. Synchronous multiplexed NOR/PSRAM read timings

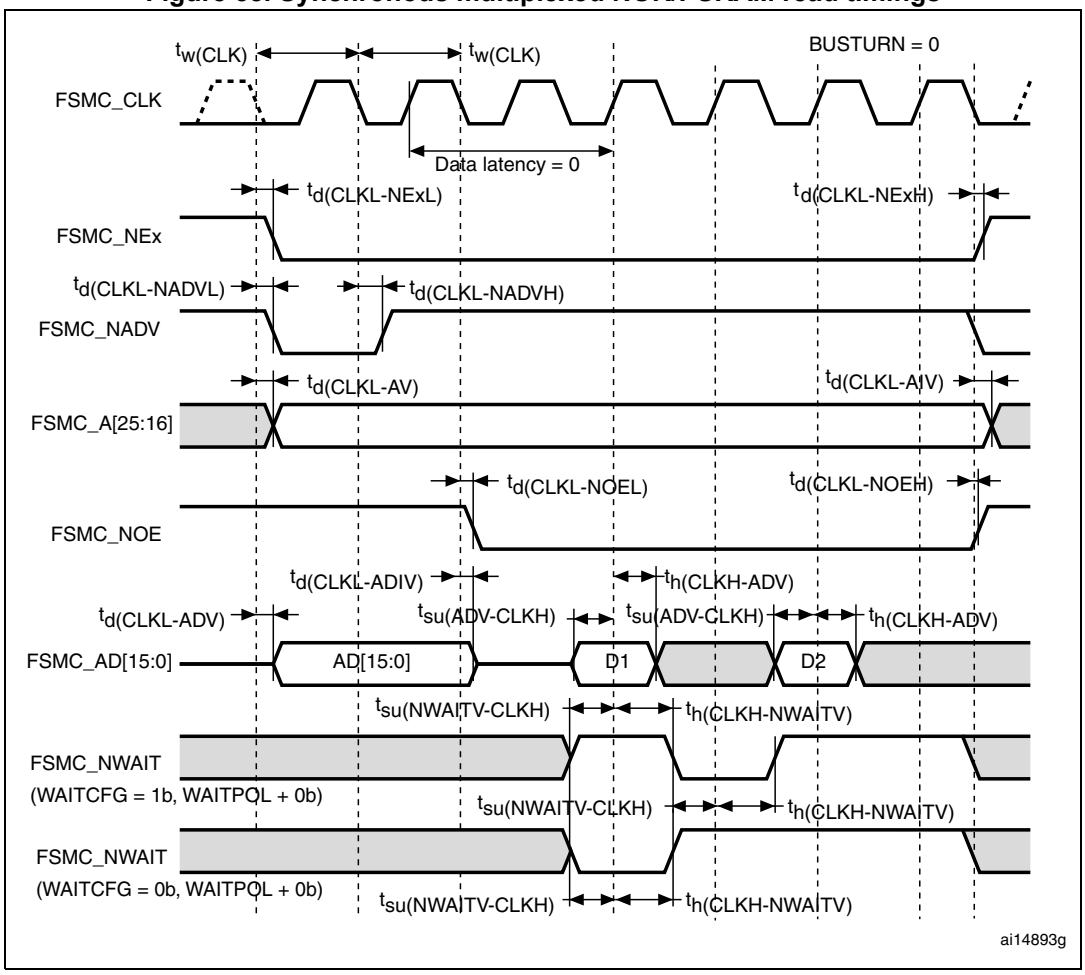


Figure 67. PC Card/CompactFlash controller waveforms for I/O space write access

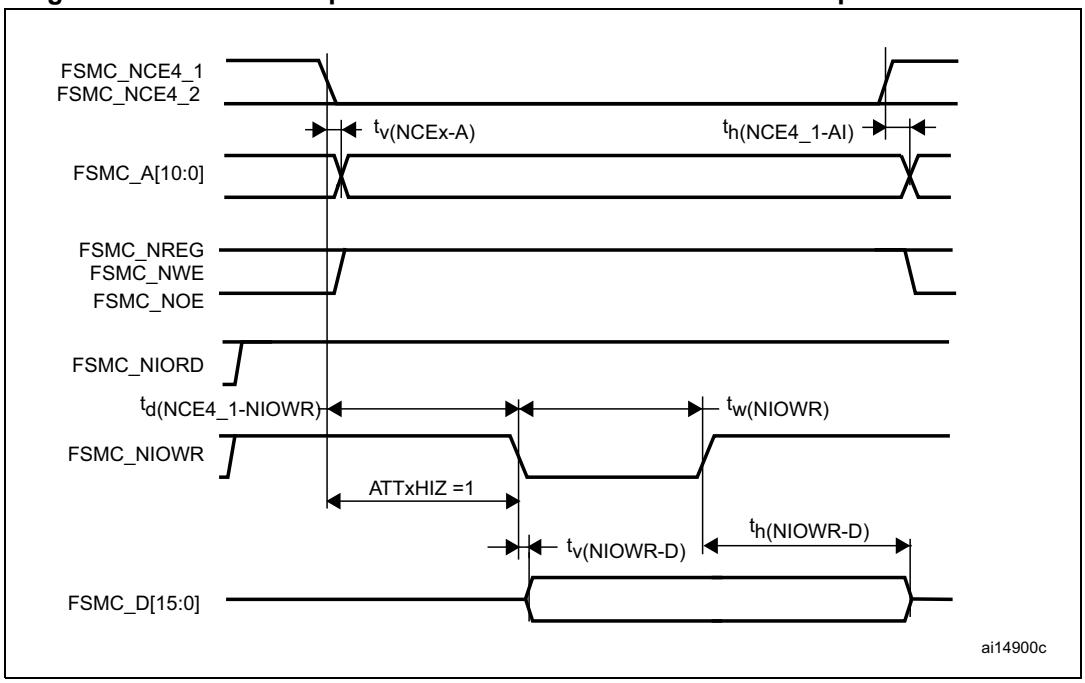


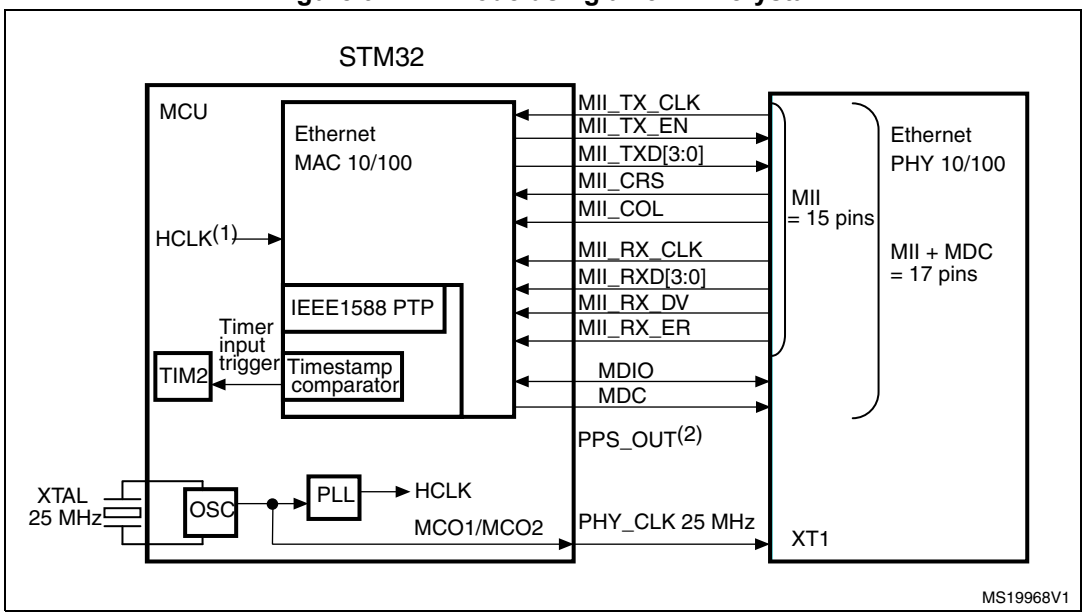
Table 83. Switching characteristics for PC Card/CF read and write cycles in attribute/common space(1)(2)

Symbol	Parameter	Min	Max	Unit
$t_{v(NCEx-A)}$	FSMC_Ncex low to FSMC_Ay valid	-	0	ns
$t_{h(NCEx\_AI)}$	FSMC_NCEx high to FSMC_Ax invalid	4	-	ns
$t_{d(NREG-NCEx)}$	FSMC_NCEx low to FSMC_NREG valid	-	3.5	ns
$t_{h(NCEx-NREG)}$	FSMC_NCEx high to FSMC_NREG invalid	T_{HCLK}+4	-	ns
$t_{d(NCEx-NWE)}$	FSMC_NCEx low to FSMC_NWE low	-	$5T_{HCLK}$+0.5	ns
$t_{d(NCEx-NOE)}$	FSMC_NCEx low to FSMC_NOE low	-	$5T_{HCLK}$ +0.5	ns
$t_{w(NOE)}$	FSMC_NOE low width	$8T_{HCLK}$–1	$8T_{HCLK}$+1	ns
$t_{d(NOE\_NCEx)}$	FSMC_NOE high to FSMC_NCEx high	$5T_{HCLK}$+2.5	-	ns
$t_{su\ (D-NOE)}$	FSMC_D[15:0] valid data before FSMC_NOE high	4.5	-	ns
$t_{h(N0E-D)}$	FSMC_N0E high to FSMC_D[15:0] invalid	3	-	ns
$t_{w(NWE)}$	FSMC_NWE low width	$8T_{HCLK}$–0.5	$8T_{HCLK}$+ 3	ns
$t_{d(NWE\_NCEx)}$	FSMC_NWE high to FSMC_NCEx high	$5T_{HCLK}$–1	-	ns
$t_{d(NCEx-NWE)}$	FSMC_NCEx low to FSMC_NWE low	-	$5T_{HCLK}$+ 1	ns
$t_{v(NWE-D)}$	FSMC_NWE low to FSMC_D[15:0] valid	-	0	ns
t_h (NWE-D)	FSMC_NWE high to FSMC_D[15:0] invalid	$8T_{HCLK}$ –1	-	ns
t_d (D-NWE)	FSMC_D[15:0] valid before FSMC_NWE high	$13T_{HCLK}$ –1	-	ns

1. C_L = 30 pF.
2. Guaranteed by characterization.

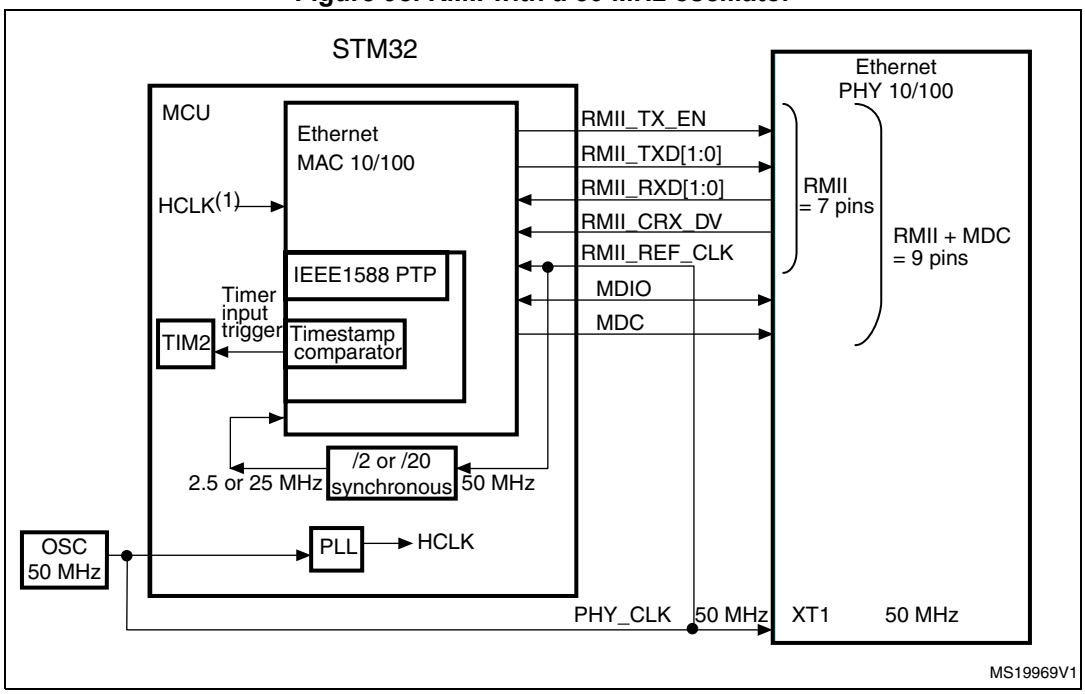
A.3 Ethernet interface solutions

Figure 97. MII mode using a 25 MHz crystal



1. f_{HCLK} must be greater than 25 MHz.
2. Pulse per second when using IEEE1588 PTP optional signal.

Figure 98. RMII with a 50 MHz oscillator



1. f_{HCLK} must be greater than 25 MHz.

Table 100. Document revision history (continued)

Date	Revision	Changes
31-May-2012	3 (continued)	Removed f_{HSE_ext} typical value in *Table 30: High-speed external user clock characteristics*. Updated *Table 32: HSE 4-26 MHz oscillator characteristics* and *Table 33: LSE oscillator characteristics (fLSE = 32.768 kHz)*. Added f_{PLL48_OUT} maximum value in *Table 36: Main PLL characteristics*. Modified equation 1 and 2 in *Section 5.3.11: PLL spread spectrum clock generation (SSCG) characteristics*. Updated *Table 39: Flash memory characteristics*, *Table 40: Flash memory programming*, and *Table 41: Flash memory programming with VPP*. Updated *Section : Output driving current*. *Table 56: I^2C characteristics*: *Note 4* updated and applied to $t_{h(SDA)}$ in Fast mode, and removed note 4 related to $t_{h(SDA)}$ minimum value. Updated *Table 67: ADC characteristics*. Updated note concerning ADC accuracy vs. negative injection current below *Table 68: ADC accuracy at fADC = 30 MHz*. Added WLCSP90 thermal resistance in *Table 98: Package thermal characteristics*. Updated *Table 90: WLCSP90 - 4.223 x 3.969 mm, 0.400 mm pitch wafer level chip scale package mechanical data*. Updated *Figure 87: UFBGA176+25 ball, 10 x 10 mm, 0.65 mm pitch, ultra fine pitch ball grid array package outline* and *Table 95: UFBGA176+25 ball, 10 × 10 × 0.65 mm pitch, ultra thin fine pitch ball grid array mechanical data*. Added *Figure 91: LQFP176 - 176-pin, 24 x 24 mm low profile quad flat recommended footprint*. Removed 256 and 768 Kbyte Flash memory density from *Table 99: Ordering information scheme*.